

Listing of the Claims

1. (Original) A method comprising:

    exposing a semiconductor wafer to a first mask part that is at least partially defective; and,

    exposing the semiconductor wafer to a second mask part corresponding to the first mask part and that is at least substantially free from defects or with defects at different locations.

2. (Original) The method of claim 1, wherein the first mask part and the second mask part are on a same photomask.

3. (Original) The method of claim 1, wherein the first mask part and the second mask part are on different photomasks.

4. (Original) The method of claim 1, further comprising exposing the semiconductor wafer to the second mask part a second time.

5. (Original) The method of claim 4, further comprising exposing the semiconductor wafer to the second mask part a third time.

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6. (Original) The method of claim 1, further comprising exposing the semiconductor wafer to the second mask part one or more additional times.

7. (Original) The method of claim 1 further comprising exposing the semiconductor wafer to the second, a third and other additional mask parts one or more additional times.

8. (Original) The method of claim 1, wherein the first mask part comprises a layout for a semiconductor device that is at least partially defective, and the second mask part comprises a layout for the semiconductor device that is at least substantially free from defects or with defects at different locations.

9. (Original) The method of claim 1, wherein exposing the semiconductor wafer to the first mask part and exposing the semiconductor wafer to the second mask part are part of a lithographic semiconductor fabrication process.

10. - 23. (Cancelled)